

RJK0208DPA

25V, 65A, 2.0mΩ max.

Built in SBD N Channel Power MOS FET
High Speed Power Switching

R07DS0942EJ0400

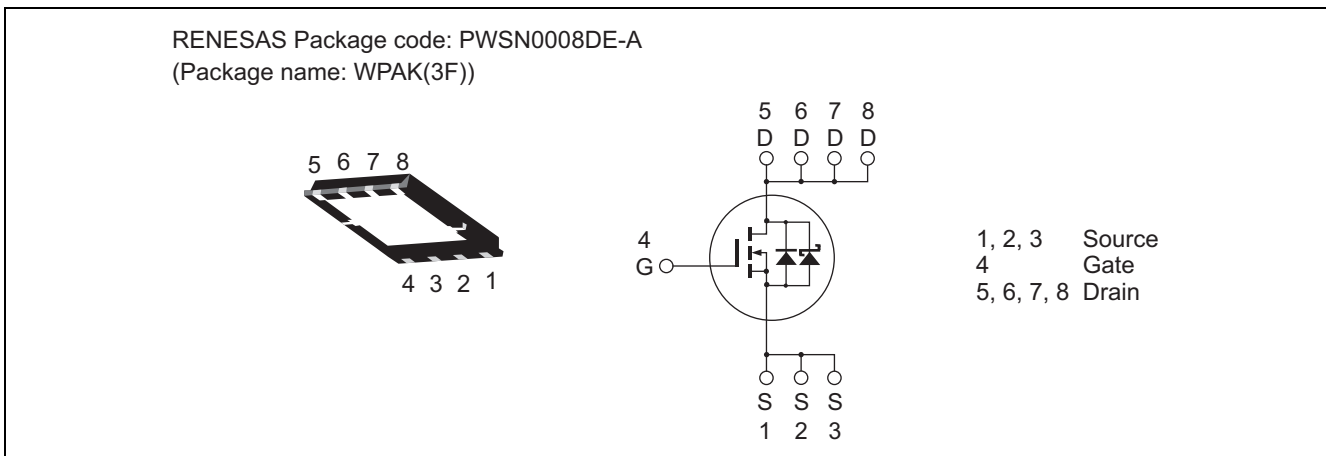
Rev.4.00

Mar 21, 2013

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|--|--|-------------|------|
| Drain to source voltage | V _{DSS} | 25 | V |
| Gate to source voltage | V _{GSS} | ±20 | V |
| Drain current | I _D | 65 | A |
| Drain peak current | I _{D(pulse)} ^{Note1} | 260 | A |
| Body-drain diode reverse drain current | I _{DR} | 65 | A |
| Avalanche current | I _{AP} ^{Note 2} | 29 | A |
| Avalanche energy | E _{AR} ^{Note 2} | 105 | mJ |
| Channel dissipation | P _{ch} ^{Note3} | 60 | W |
| Channel to case thermal impedance | θ _{ch-c} ^{Note3} | 2.08 | °C/W |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

3. T_c = 25°C

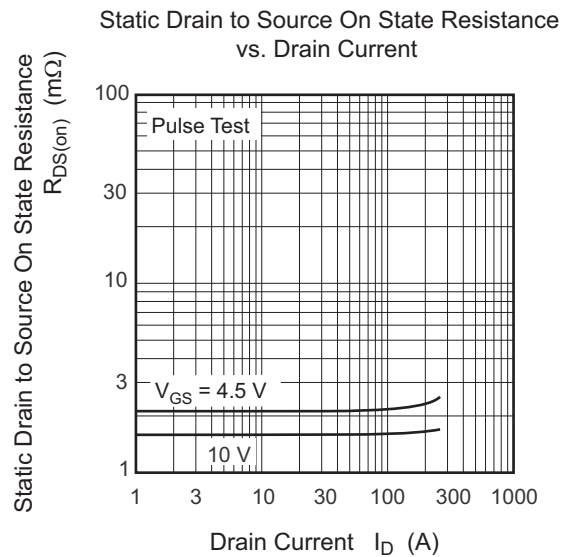
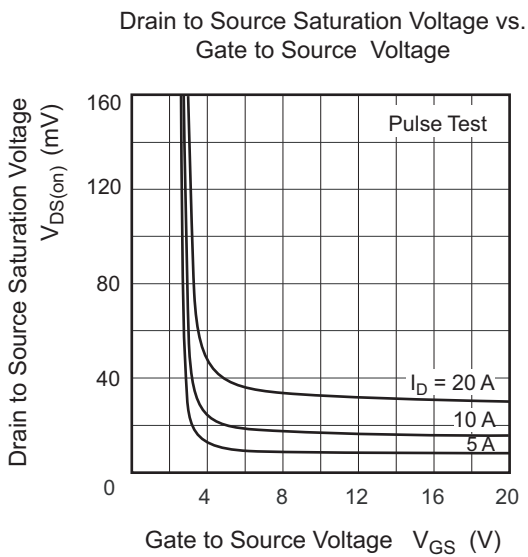
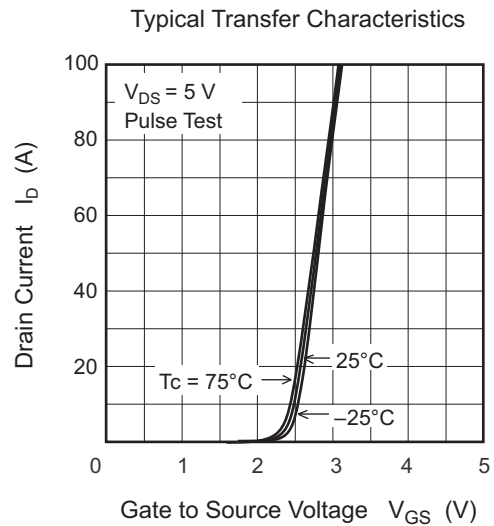
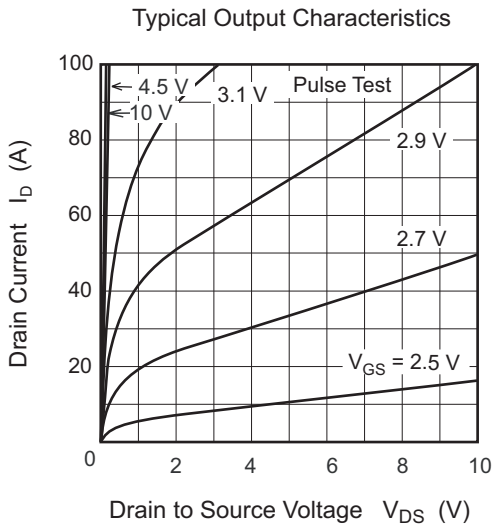
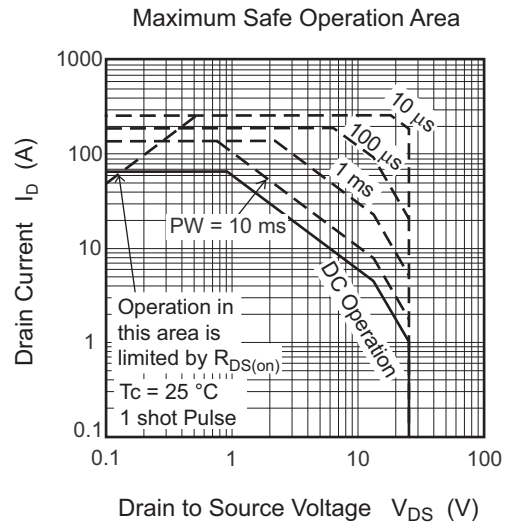
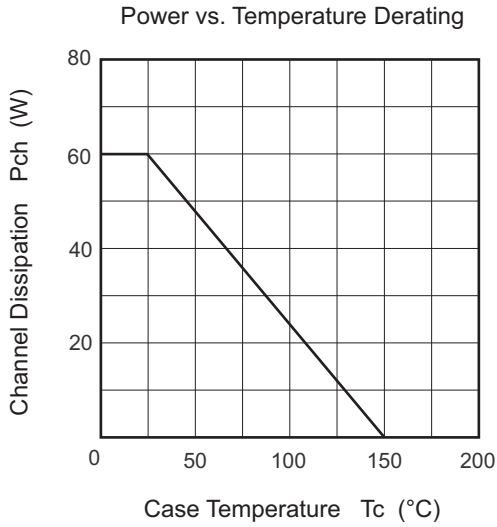
Electrical Characteristics

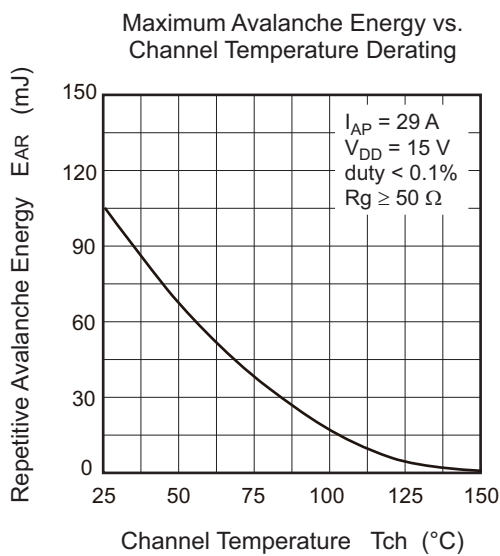
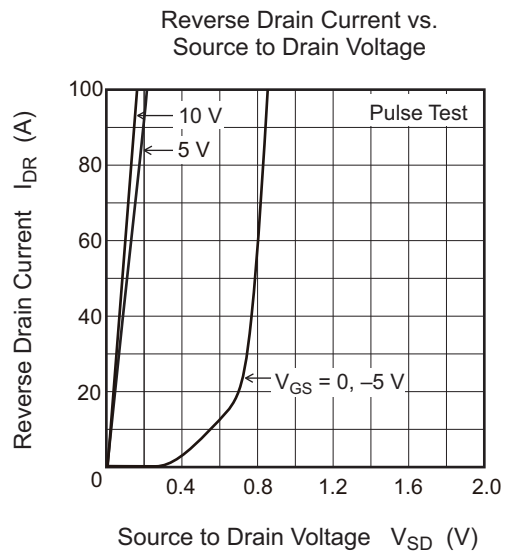
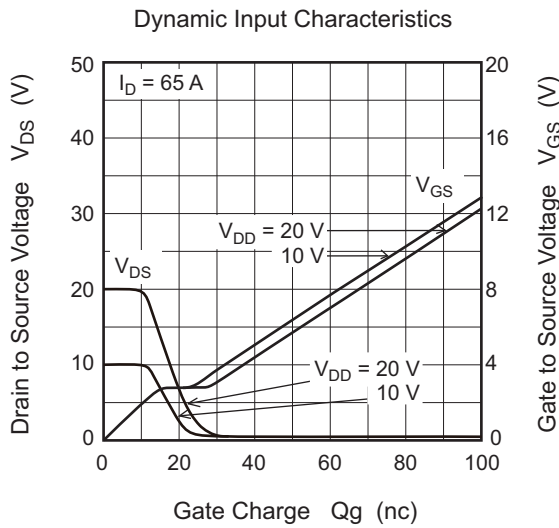
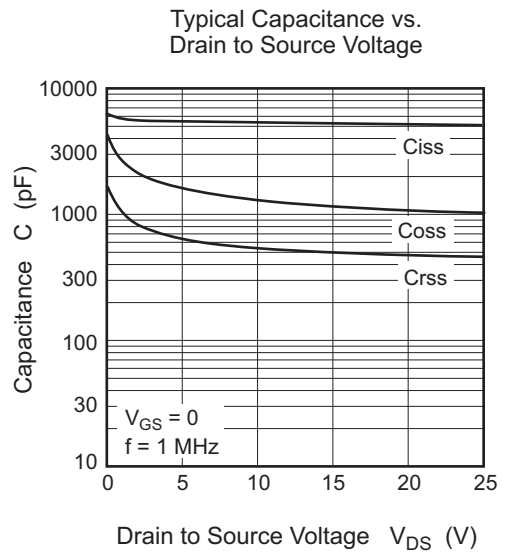
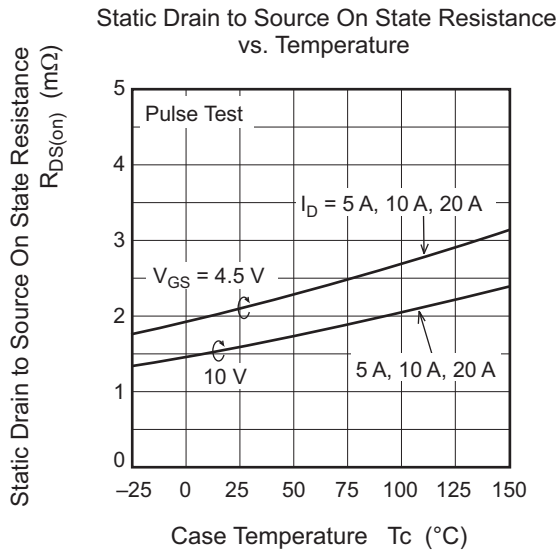
(Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|--|---------------|-----|------|-----------|---------------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 25 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 0.5 | μA | $V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 1 | mA | $V_{DS} = 25 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.2 | — | 2.5 | V | $V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 1.6 | 2.0 | m Ω | $I_D = 32.5\text{A}$, $V_{GS} = 10 \text{ V}$ ^{Note4} |
| | $R_{DS(on)}$ | — | 2.1 | 2.7 | m Ω | $I_D = 32.5\text{A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note4} |
| Forward transfer admittance | $ y_{fs} $ | — | 125 | — | S | $I_D = 32.5\text{A}$, $V_{DS} = 5 \text{ V}$ ^{Note4} |
| Input capacitance | C_{iss} | — | 5350 | 7490 | pF | $V_{DS} = 10 \text{ V}$ |
| Output capacitance | C_{oss} | — | 1290 | — | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | C_{rss} | — | 530 | — | pF | $f = 1 \text{ MHz}$ |
| Gate Resistance | R_g | — | 1.6 | 3.2 | Ω | |
| Total gate charge | Q_g | — | 36.0 | — | nC | $V_{DD} = 10 \text{ V}$ |
| Gate to source charge | Q_{gs} | — | 15.3 | — | nC | $V_{GS} = 4.5 \text{ V}$ |
| Gate to drain charge | Q_{gd} | — | 10.0 | — | nC | $I_D = 65 \text{ A}$ |
| Turn-on delay time | $t_{d(on)}$ | — | 21 | — | ns | $V_{GS} = 10 \text{ V}$, $I_D = 32.5 \text{ A}$ |
| Rise time | t_r | — | 8 | — | ns | $V_{DD} \cong 10 \text{ V}$ |
| Turn-off delay time | $t_{d(off)}$ | — | 80 | — | ns | $R_L = 0.31 \Omega$ |
| Fall time | t_f | — | 17 | — | ns | $R_g = 4.7 \Omega$ |
| Body-drain diode forward voltage | V_{DF} | — | 0.39 | — | V | $I_F = 2 \text{ A}$, $V_{GS} = 0$ ^{Note4} |
| Body-drain diode reverse recovery time | t_{rr} | — | 45 | — | ns | $I_F = 65 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

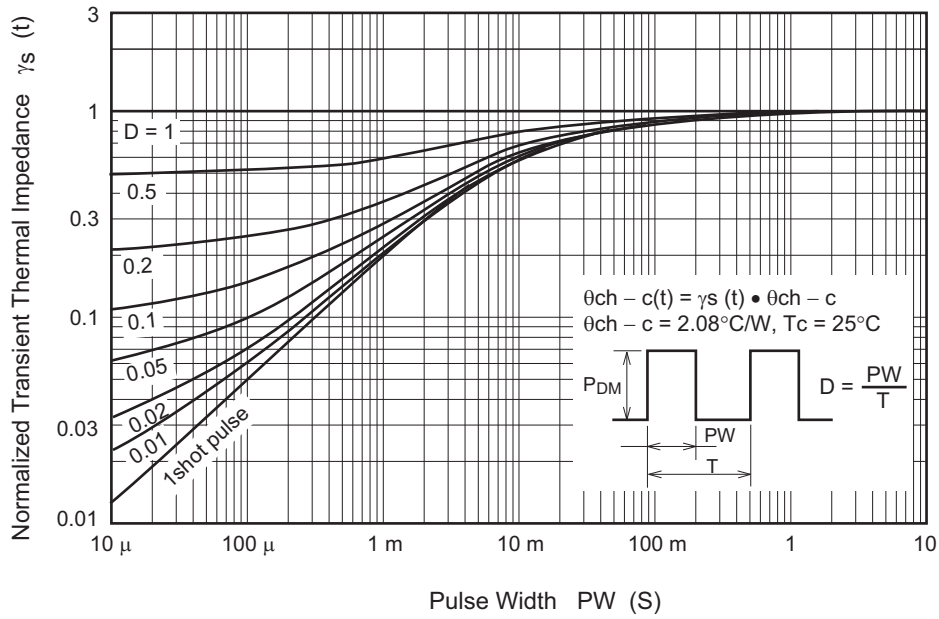
Notes: 4. Pulse test

Main Characteristics

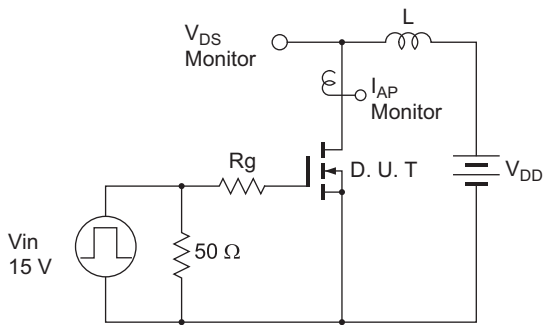




Normalized Transient Thermal Impedance vs. Pulse Width

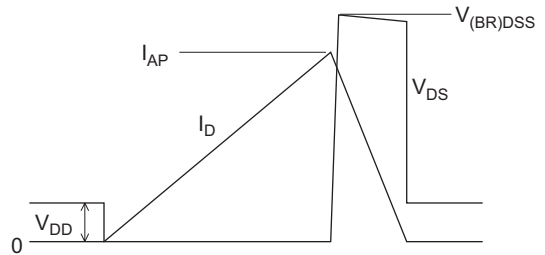


Avalanche Test Circuit

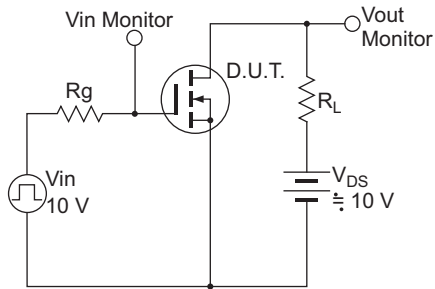


Avalanche Waveform

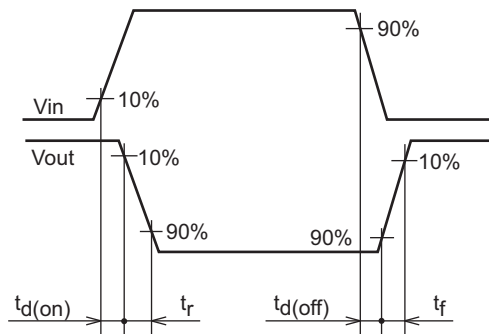
$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Switching Time Test Circuit



Switching Time Waveform



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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-3390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Laviel' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141